

# matched dual n-channel JFET designed for . . .

**Performance Curves NZF-D, NNZ**  
See Section 4

## ■ Wideband Differential Amplifiers

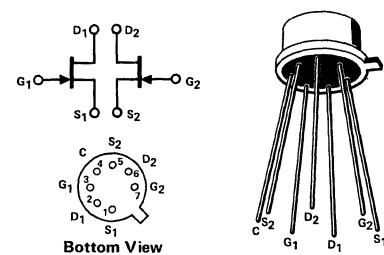
### BENEFITS

- High Gain through 100 MHz  
 $g_{fs} = 4500 \mu\text{mho}$  Minimum
- Matching Characteristics Specified

### ABSOLUTE MAXIMUM RATINGS (25°C)

|  |                                     |                |
|--|-------------------------------------|----------------|
| Gate-Drain or Gate-Source Voltage                        | .....                               | -25 V          |
| Gate Current   | .....                               | 50 mA          |
| Device Dissipation (Each Side), $T_A = 85^\circ\text{C}$ | (Derate 3.85 mW/ $^\circ\text{C}$ ) | 250 mW         |
| Total Device Dissipation, $T_A = 85^\circ\text{C}$       | (Derate 7.7 mW/ $^\circ\text{C}$ )  | 500 mW         |
| Storage Temperature Range                                | .....                               | -65 to + 200°C |
| Lead Temperature<br>(1/16" from case for 10 seconds)     | .....                               | 300°C          |

TO-78  
See Section 6



### ELECTRICAL CHARACTERISTICS (25° unless otherwise noted)

| Characteristic                          |  | Min  | Max    | Unit                                 | Test Conditions                                |                       |  |
|---|--|------|--------|--------------------------------------|--|-----------------------|--|
| 1<br>S<br>T<br>A<br>T<br>I<br>C         | $I_{GSS}$<br>Gate Reverse Current  |      | -100   | pA                                   | $V_{GS} = -15 \text{ V}$ , $V_{DS} = 0$        | $150^\circ\text{C}$   |  |
|   |  |      | -250   | nA                                   |  |                       |  |
| 3<br>B<br>V<br>G<br>S<br>S              | $BV_{GSS}$<br>Gate-Source Breakdown Voltage                                | -25  |        | V                                    | $I_G = -1 \mu\text{A}$ , $V_{DS} = 0$          |                       |  |
| 4<br>T<br>I<br>C<br>I<br>C              | $V_{GS(\text{off})}$<br>Gate-Source Cutoff Voltage                         | -1   | -5     | V                                    | $V_{DS} = 10 \text{ V}$ , $I_D = 1 \text{ nA}$ |                       |  |
| 5<br>I<br>D<br>S<br>S                   | $I_{DSS}$<br>Saturation Drain Current (Note 1)                             | 5    | 40     | mA                                   | $V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$         |                       |  |
| 6<br>g<br>f<br>s                        | $g_{fs}$<br>Common-Source Forward Transconductance                         | 4500 | 10,000 | $\mu\text{mho}$                      | $V_{DS} = 10 \text{ V}$ , $I_D = 5 \text{ mA}$ | $f = 1 \text{ kHz}$   |  |
| 7<br>g<br>f<br>s                        | $g_{fs}$<br>Common-Source Forward Transconductance                         | 4500 | 10,000 |                                      |  | $f = 100 \text{ MHz}$ |  |
| 8<br>g<br>o<br>s                        | $g_{os}$<br>Common-Source Output Conductance                               |      | 200    |                                      |  | $f = 1 \text{ kHz}$   |  |
| 9<br>g<br>o<br>s                        | $g_{os}$<br>Common-Source Output Conductance                               |      | 200    |                                      |  | $f = 100 \text{ MHz}$ |  |
| 10<br>C<br>i<br>s<br>s                  | $C_{iss}$<br>Common-Source Input Capacitance                               |      | 5      | $\text{pF}$                          | $V_{DG} = 10 \text{ V}$ , $I_D = 5 \text{ mA}$ | $f = 1 \text{ MHz}$   |  |
| 11<br>C<br>r<br>s<br>s                  | $C_{rss}$<br>Common-Source Reverse Transfer Capacitance                    |      | 1.2    |                                      |  | $f = 10 \text{ kHz}$  |  |
| 12<br>$\bar{e}_n$                       | Equivalent Short Circuit Input Noise Voltage                               |      | 30     | $\frac{\text{nV}}{\sqrt{\text{Hz}}}$ |  |                       |  |
| 13<br>M<br>A<br>A<br>I<br>D<br>S<br>S   | $I_{DSS1}$<br>$I_{DSS2}$<br>Saturation Drain Current Ratio (Notes 1 and 2) | 0.85 | 1      |                                      | $V_{DS} = 10 \text{ V}$ , $V_{GS} = 0$         |                       |  |
| 14<br>T<br>C<br>H<br>I<br>N<br>G        | $ V_{GS1}-V_{GS2} $<br>Differential Gate-Source Voltage                    |      | 100    | mV                                   | $V_{DG} = 10 \text{ V}$ , $I_D = 5 \text{ mA}$ | $f = 1 \text{ kHz}$   |  |
| 15<br>g<br>f<br>s<br>1                  | $g_{f1}$   | 0.85 | 1      |                                      |  |                       |  |
| 15<br>g<br>f<br>s<br>2                  | $g_{f2}$   |      |        |                                      |  |                       |  |
| 16<br>g<br>o<br>s<br>1-g<br>o<br>s<br>2 | $g_{os1-g_{os2}}$<br>Differential Output Conductance                       |      | 20     | $\mu\text{mho}$                      |  |                       |  |

#### NOTES:

1. Pulse test required, pulse width = 300  $\mu\text{s}$ , duty cycle  $\leq 30\%$ .
2. Assumes smaller value in numerator.

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